

### **FEATURES**

- Operates With 3-V to 5.5-V V<sub>CC</sub> Supply
- Operates up to 1 Mbit/s
- Low Standby Current . . . 1 μA Typ
- External Capacitors . . . 4 × 0.1 µF
- Accepts 5-V Logic Input With 3.3-V Supply
- RS-232 Bus-Pin ESD Protection Exceeds ±15 kV Using Human-Body Model (HBM)
- Auto-Powerdown Feature Automatically Disables Drivers for Power Savings

### **APPLICATIONS**

- Battery-Powered, Hand-Held, and Portable
  Equipment
- PDAs and Palmtop PCs
- Notebooks, Sub-Notebooks, and Laptops
- Digital Cameras
- Mobile Phones and Wireless Devices

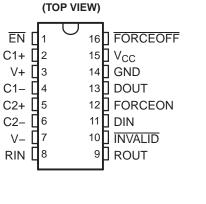
### **DESCRIPTION/ORDERING INFORMATION**

The TRSF3221 consists of one line driver, one line receiver, and a dual charge-pump circuit with ±15-kV IEC ESD protection pin-to-pin (serial-port connection pins, including GND). The TRSF3221 provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The TRSF3221 operates at data signaling rates up to 1 Mbit/s and a driver output slew rate of 24 V/µs to 150 V/µs.

Flexible control options for power management are available when the serial port is inactive. The auto-powerdown feature functions when FORCEON is low and FORCEOFF is high. During this mode of operation, if the TRSF3221 does not sense a valid RS-232 signal on the receiver input, the driver output is disabled. If FORCEOFF is set low and the enable ( $\overline{EN}$ ) input is high, both the driver and receiver are shut off, and the supply current is reduced to 1  $\mu$ A. Disconnecting the serial port or turning off the peripheral drivers causes the auto-powerdown condition to occur. Auto-powerdown can be disabled when FORCEON and FORCEOFF are high. With auto-powerdown enabled, the device is activated automatically when a valid signal is applied to the receiver input. The INVALID output notifies the user if an RS-232 signal is present at the receiver input. INVALID is high (valid data) if the receiver input voltage is greater than 2.7 V or less than -2.7 V, or has been between -0.3 V and 0.3 V for more than 30  $\mu$ s. See Figure 5 for receiver input levels.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



**DB OR PW PACKAGE** 



#### **ORDERING INFORMATION**

T <sub>A</sub>	PAC	KAGE <sup>(1)(2)</sup>	ORDERABLE PART NUMBER	TOP-SIDE MARKING
	SSOP – DB	Reel of 2000	TRSF3221CDBR	RT21C
0°C to 70°C		Tube of 90	TRSF3221CPW	RT21C
	TSSOP – PW	Reel of 2000	TRSF3221CPWR	- RIZIC
	SSOP – DB	Reel of 2000	TRSF3221IDBR	RT21I
–40°C to 85°C		Tube of 90	TRSF3221IPW	DTO4
	TSSOP – PW	Reel of 2000	TRSF3221IPWR	— RT21I

(1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

(2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

#### **FUNCTION TABLES**

Each Driver<sup>(1)</sup>

	I	NPUTS		OUTPUT	
DIN	FORCEON	FORCEOFF	VALID RIN RS-232 LEVEL	DOUT	DRIVER STATUS
Х	Х	L	Х	Z	Powered off
L	Н	Н	Х	Н	Normal operation with
Н	Н	н	Х	L	auto-powerdown disabled
L	L	н	Yes	Н	Normal operation with
Н	L	н	Yes	L	auto-powerdown enabled
L	L	Н	No	Z	Powered off by
Н	L	Н	No	Z	auto-powerdown feature

(1) H = high level, L = low level, X = irrelevant, Z = high impedance

#### Each Receiver<sup>(1)</sup>

	INPU	TS	OUTPUT
RIN	EN	VALID RIN RS-232 LEVEL	ROUT
L	L	Х	Н
н	L	Х	L
х	н	Х	Z
Open	L	No	Н

(1) H = high level, L = low level, X = irrelevant, Z = high impedance (off), Open = disconnected input or connected driver off

#### LOGIC DIAGRAM (POSITIVE LOGIC) 13 11 DIN DOUT 16 FORCEOFF 10 INVALID Auto-Powerdown 12 FORCEON -9 8 ROUT RIN П 1 \_\_\_\_ EN



### Absolute Maximum Ratings<sup>(1)</sup>

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range <sup>(2)</sup>		-0.3	6	V
V+	Positive-output supply voltage range <sup>(2)</sup>		-0.3	7	V
V–	egative-output supply voltage range <sup>(2)</sup>		0.3	-7	V
V+ - V-	Supply voltage difference <sup>(2)</sup>			13	V
V	Input voltage range	Driver (FORCEOFF, FORCEON, EN)	-0.3	6	V
V <sub>I</sub> I		Receiver	-25	25	v
N/		Driver	-13.2	13.2	V
Vo	Output voltage range	Receiver (INVALID)	-0.3	V <sub>CC</sub> + 0.3	v
0	Declares the survey line or denses $(3)(4)$	DB package		82	0000
$\theta_{JA}$	Package thermal impedance <sup>(3)(4)</sup>	PW package		108	°C/W
TJ	Operating virtual junction temperature			150	°C
T <sub>stg</sub>	Storage temperature range		-65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

All voltages are with respect to network GND. (2)

(3)Maximum power dissipation is a function of  $T_J(max)$ ,  $\theta_{JA}$ , and  $T_A$ . The maximum allowable power dissipation at any allowable ambient temperature is  $P_D = (T_J(max) - T_A)/\theta_{JA}$ . Operating at the absolute maximum  $T_J$  of 150°C can affect reliability.

The package thermal impedance is calculated in accordance with JESD 51-7. (4)

#### Recommended Operating Conditions<sup>(1)</sup>

#### See Figure 6

				MIN	NOM	MAX	UNIT
	Supply voltage		$V_{CC} = 3.3 V$	3	3.3	3.6	V
	Supply voltage		$V_{CC} = 5 V$	4.5	5	5.5	v
V	Driver and control	DIN, FORCEOFF, FORCEON, EN	$V_{CC} = 3.3 V$	2			V
V <sub>IH</sub>	<sup>/IH</sup> high-level input voltage	DIN, FORCEOFF, FORCEON, EN	$V_{CC} = 5 V$	2.4			v
$V_{\text{IL}}$	Driver and control low-level input voltage	DIN, FORCEOFF, FORCEON, EN				0.8	V
VI	Driver and control input voltage	DIN, FORCEOFF, FORCEON		0		5.5	V
VI	Receiver input voltage			-25		25	V
т	Operating free air temperature		TRSF32211	-40		85	°C
Τ <sub>Α</sub>	Operating free-air temperature		TRSF3221C	0		70	C

(1) Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V ± 0.5 V.

#### Electrical Characteristics<sup>(1)</sup>

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 6)

	PARA	METER	TEST CONDITIONS	MIN	TYP <sup>(2)</sup>	MAX	UNIT
l <sub>l</sub>	Input leakage current	FORCEOFF, FORCEON, EN			±0.01	±1	μA
		Auto-powerdown disabled	No load, FORCEOFF and FORCEON at $V_{CC}$		0.3	1	mA
lee	Supply current	Powered off	No load, FORCEOFF at GND		1	10	
ICC	(T <sub>A</sub> = 25°C)	Auto-powerdown enabled	No load, FORCEOFF at V <sub>CC</sub> , FORCEON at GND, All RIN are open or grounded		1	10	μA

Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V ± 0.5 V. All typical values are at V<sub>CC</sub> = 3.3 V or V<sub>CC</sub> = 5 V, and T<sub>A</sub> = 25°C. (1)

(2)



#### **DRIVER SECTION**

#### Electrical Characteristics<sup>(1)</sup>

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 6)

	PARAMETER	TEST	CONDITIONS		MIN	TYP <sup>(2)</sup>	MAX	UNIT
V <sub>OH</sub>	High-level output voltage	DOUT at $R_L = 3 k\Omega$ to GND,	DIN = GND		5	5.4		V
V <sub>OL</sub>	Low-level output voltage	DOUT at $R_L = 3 k\Omega$ to GND,	$DIN = V_{CC}$		-5	-5.4		V
I <sub>IH</sub>	High-level input current	$V_I = V_{CC}$				±0.01	±1	μA
$I_{IL}$	Low-level input current	V <sub>I</sub> at GND				±0.01	±1	μA
	Short-circuit	V 0.V	$V_{CC} = 3.6 V$			±35	±60	~ ^
IOS	output current <sup>(3)</sup>	$V_{O} = 0 V$	$V_{CC} = 5.5 V$			±35	±90	mA
r <sub>o</sub>	Output resistance	$V_{CC}$ , V+, and V- = 0 V,	$V_0 = \pm 2 V$		300	10M		Ω
		FORCEOFF = GND	$V_{O} = \pm 12 V$ ,	$V_{CC}$ = 3 V to 3.6 V			±25	
l <sub>off</sub>	Output leakage current	FURGEOFF = GND	$V_{O} = \pm 10 V$ ,	$V_{CC}$ = 4.5 V to 5.5 V			±25	μA

 Test conditions are C1-C4 = 0.1 μF at V<sub>CC</sub> = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2-C4 = 0.33 μF at V<sub>CC</sub> = 5 V ± 0.5 V.
 All typical values are at V<sub>CC</sub> = 3.3 V or V<sub>CC</sub> = 5 V, and T<sub>A</sub> = 25°C.
 Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one extended to a should be absolute to the shou output should be shorted at a time.

### Switching Characteristics<sup>(1)</sup>

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 6)

F	PARAMETER		TEST CONDITIONS		MIN	TYP <sup>(2)</sup>	MAX	UNIT
Maximum data rate (see Figure 1)			C <sub>L</sub> = 1000 pF		250			
		$R_L = 3 k\Omega$	C <sub>L</sub> = 250 pF,	$V_{CC}$ = 3 V to 4.5 V	1000			kbit/s
(00011	guio i)		$C_{L} = 1000 \text{ pF},$	$V_{CC}$ = 4.5 V to 5.5 V	1000			
t <sub>sk(p)</sub>	Pulse skew <sup>(3)</sup>	$C_{L} = 150 \text{ pF} \text{ to } 2500 \text{ pF},$	$R_L = 3 k\Omega$ to 7 k $\Omega$ ,	See Figure 2		100		ns
SR(tr)	Slew rate, transition region (see Figure 1)	V <sub>CC</sub> = 3.3 V,	$R_L = 3 k\Omega$ to 7 k $\Omega$ ,	C <sub>L</sub> = 150 pF to 1000 pF	18		150	V/µs

Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V ± 0.5 V. All typical values are at V<sub>CC</sub> = 3.3 V or V<sub>CC</sub> = 5 V, and T<sub>A</sub> = 25°C. Pulse skew is defined as |t<sub>PLH</sub> - t<sub>PHL</sub>| of each channel of the same device. (1)

(2)

(3)

#### **ESD** Protection

TERMI	NAL	TEST CONDITIONS	тур	UNIT
TERMINAL         TEST CONDITIONS           NAME         NO.         TEST CONDITIONS           DOUT         13         HBM	TEST CONDITIONS	ITP	UNIT	
DOUT		НВМ	±15	kV

### **RECEIVER SECTION**

### Electrical Characteristics<sup>(1)</sup>

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 6)

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(2)</sup>	MAX	UNIT
V <sub>OH</sub>	High-level output voltage	$I_{OH} = -1 \text{ mA}$	$V_{CC} - 0.6$	$V_{CC} - 0.1$		V
V <sub>OL</sub>	Low-level output voltage	I <sub>OL</sub> = 1.6 mA			0.4	V
V	Desitive going input threshold veltage	$V_{CC} = 3.3 V$		1.6	2.4	V
V <sub>IT+</sub>	Positive-going input threshold voltage	$V_{CC} = 5 V$		1.9	2.4	v
v	Negative going input threshold voltage	V <sub>CC</sub> = 3.3 V	0.6	1.1		V
V <sub>IT–</sub>	Negative-going input threshold voltage	$V_{CC} = 5 V$	0.8	1.4		v
V <sub>hys</sub>	Input hysteresis (V <sub>IT+</sub> - V <sub>IT-</sub> )			0.5		V
I <sub>off</sub>	Output leakage current	FORCEOFF = 0 V		±0.05	±10	μA
r <sub>i</sub>	Input resistance	$V_{I} = \pm 3 \text{ V to } \pm 25 \text{ V}$	3	5	7	kΩ

(1) Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V ± 0.5 V. (2) All typical values are at V<sub>CC</sub> = 3.3 V or V<sub>CC</sub> = 5 V, and T<sub>A</sub> = 25°C.

### Switching Characteristics<sup>(1)</sup>

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 6)

	PARAMETER	TEST CONDITIONS	TYP <sup>(2)</sup>	UNIT
t <sub>PLH</sub>	Propagation delay time, low- to high-level output	C <sub>L</sub> = 150 pF, See Figure 3	150	ns
t <sub>PHL</sub>	Propagation delay time, high- to low-level output	C <sub>L</sub> = 150 pF, See Figure 3	150	ns
t <sub>en</sub>	Output enable time	$C_L = 150 \text{ pF}, R_L = 3 \text{ k}\Omega$ , See Figure 4	200	ns
t <sub>dis</sub>	Output disable time	$C_L = 150 \text{ pF}, R_L = 3 \text{ k}\Omega$ , See Figure 4	200	ns
t <sub>sk(p)</sub>	Pulse skew <sup>(3)</sup>	See Figure 3	50	ns

Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V ± 0.5 V. All typical values are at V<sub>CC</sub> = 3.3 V or V<sub>CC</sub> = 5 V, and T<sub>A</sub> = 25°C. Pulse skew is defined as  $|t_{PLH} - t_{PHL}|$  of each channel of the same device. (1)

(2)

(3)

### **ESD** Protection

TERMI	NAL	TEST CONDITIONS	тур	UNIT
NAME	NO.	TEST CONDITIONS	115	UNIT
RIN	8	НВМ	±15	kV



### **AUTO-POWERDOWN SECTION**

#### **Electrical Characteristics**

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

	PARAMETER	TEST CO	MIN	MAX	UNIT	
V <sub>T+(valid)</sub>	Receiver input threshold for INVALID high-level output voltage	FORCEON = GND,	$\overline{FORCEOFF} = V_{CC}$		2.7	V
V <sub>T-(valid)</sub>	Receiver input threshold for INVALID high-level output voltage	FORCEON = GND,	$\overline{FORCEOFF} = V_{CC}$	-2.7		V
V <sub>T(invalid)</sub>	Receiver input threshold for INVALID low-level output voltage	FORCEON = GND,	$\overline{FORCEOFF} = V_{CC}$	-0.3	0.3	V
V <sub>OH</sub>	INVALID high-level output voltage	$I_{OH} = -1 \text{ mA}, \text{ FORCEOR}$ FORCEOFF = V <sub>CC</sub>	V <sub>CC</sub> - 0.6		V	
V <sub>OL</sub>	INVALID low-level output voltage	$I_{OL} = 1.6 \text{ mA}, \text{FORCEO}$ FORCEOFF = V <sub>CC</sub>		0.4	V	

#### **Switching Characteristics**

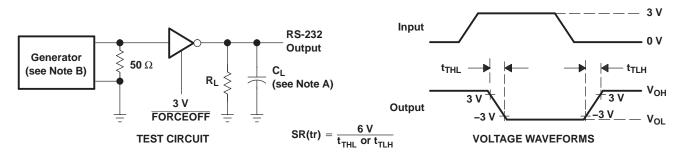
over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

	PARAMETER	TYP <sup>(1)</sup>	UNIT
t <sub>valid</sub>	Propagation delay time, low- to high-level output	1	μs
t <sub>invalid</sub>	Propagation delay time, high- to low-level output	30	μs
t <sub>en</sub>	Supply enable time	100	μs

(1) All typical values are at V<sub>CC</sub> = 3.3 V or V<sub>CC</sub> = 5 V, and T<sub>A</sub> = 25°C.



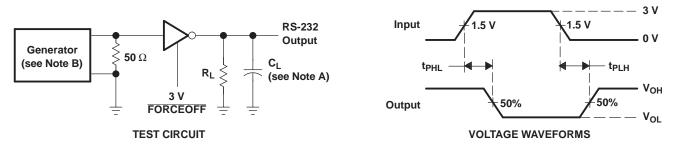
#### PARAMETER MEASUREMENT INFORMATION



NOTES: A.  $C_L$  includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_0$  = 50  $\Omega$ , 50% duty cycle,  $t_r \le 10$  ns,  $t_f \le 10$  ns.

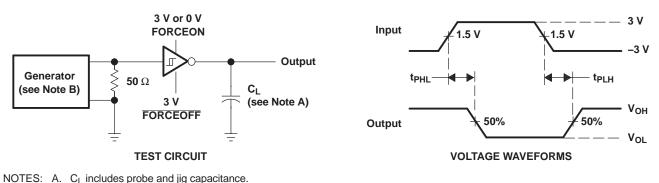
#### Figure 1. Driver Slew Rate



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_0 = 50 \Omega$ , 50% duty cycle,  $t_r \le 10$  ns,  $t_f \le 10$  ns.

#### Figure 2. Driver Pulse Skew

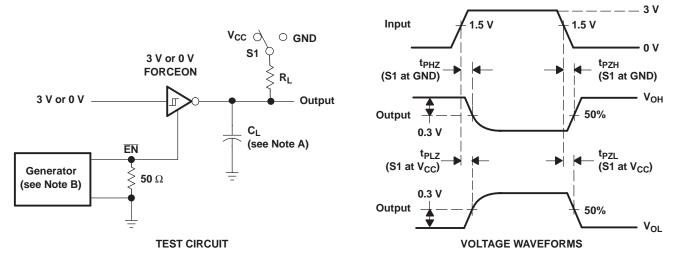


B. The pulse generator has the following characteristics:  $Z_{O} = 50 \Omega$ , 50% duty cycle,  $t_{f} \le 10$  ns,  $t_{f} \le 10$  ns.

#### Figure 3. Receiver Propagation Delay Times



#### PARAMETER MEASUREMENT INFORMATION (continued)

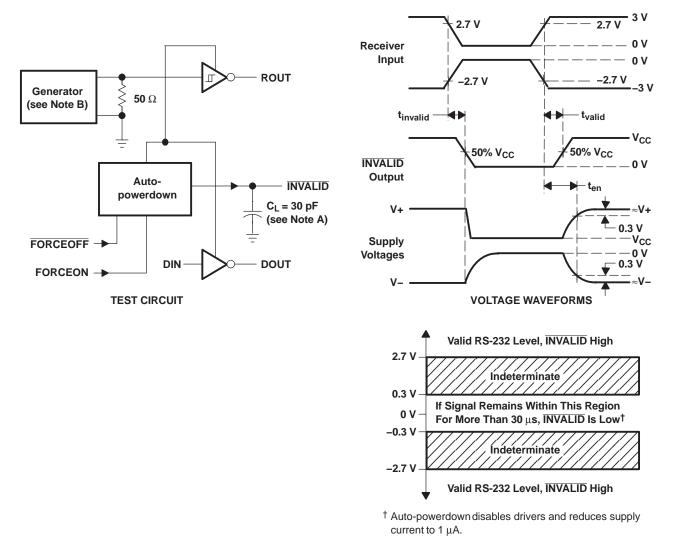


- NOTES: A. C<sub>L</sub> includes probe and jig capacitance.
  - B. The pulse generator has the following characteristics:  $Z_0 = 50 \Omega$ , 50% duty cycle,  $t_r \le 10$  ns,  $t_f \le 10$  ns.
    - $C. \hspace{0.1in} t_{PLZ} \hspace{0.1in} \text{and} \hspace{0.1in} t_{PHZ} \hspace{0.1in} \text{are the same as} \hspace{0.1in} t_{dis}.$
    - D.  $t_{\text{PZL}}$  and  $t_{\text{PZH}}$  are the same as  $t_{\text{en}}.$

#### Figure 4. Receiver Enable and Disable Times



### PARAMETER MEASUREMENT INFORMATION (continued)

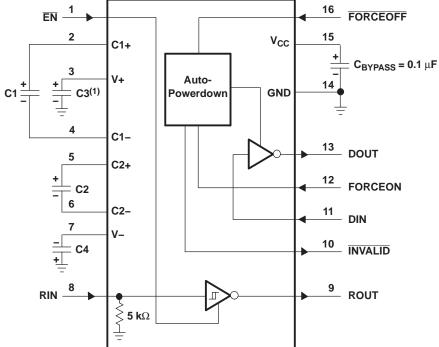


NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 5 kbit/s,  $Z_{O}$  = 50  $\Omega$ , 50% duty cycle,  $t_{r} \le 10$  ns,  $t_{f} \le 10$  ns.

#### Figure 5. INVALID Propagation Delay Times and Driver Enabling Time





(1) C3 can be connected to  $V_{\mbox{CC}}$  or GND. NOTES: A. Resistor values shown are nominal.

V <sub>CC</sub> vs CAPACITOR VALUES								
V <sub>CC</sub>	C1	C2, C3, and C4						
$\begin{array}{c} \textbf{3.3 V} \pm \textbf{0.3 V} \\ \textbf{5 V} \pm \textbf{0.5 V} \\ \textbf{3 V to 5.5 V} \end{array}$	0.1 μF 0.047 μF 0.1 μF	0.1 μF 0.33 μF 0.47 μF						

V<sub>CC</sub> vs CAPACITOR VALUES

Figure 6. Typical Operating Circuit and Capacitor Values



#### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
TRSF3221CDBR	OBSOLETE	SSOP	DB	16		TBD	Call TI	Call TI	0 to 70	RT21C	

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW**: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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# **DB0016A**



## **PACKAGE OUTLINE**

## SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not

- exceed 0.15 mm per side. 4. Reference JEDEC registration MO-150.



## DB0016A

# **EXAMPLE BOARD LAYOUT**

## SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

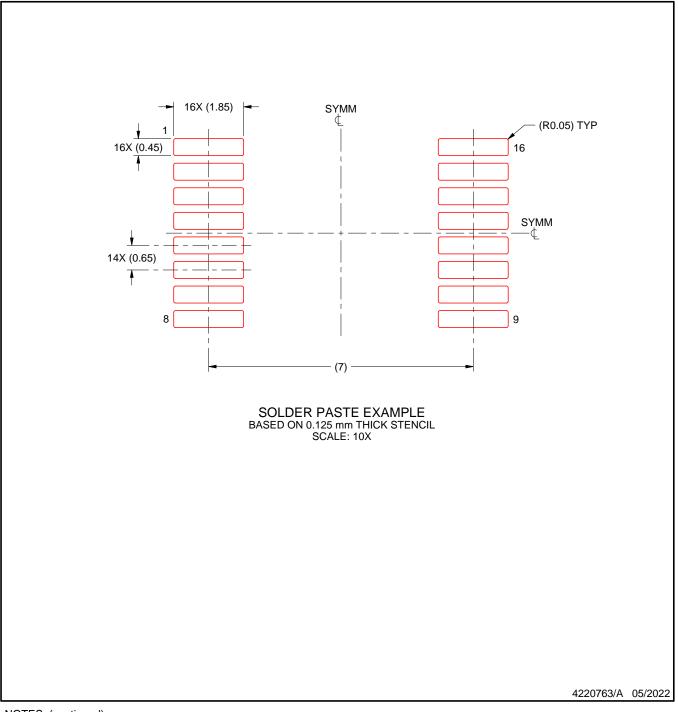


## DB0016A

# **EXAMPLE STENCIL DESIGN**

## SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

8. Board assembly site may have different recommendations for stencil design.



<sup>7.</sup> Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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